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November 2013

## **FQP24N08**

# N-Channel QFET $^{\circledR}$ MOSFET 80 V, 24 A, 60 m $\Omega$

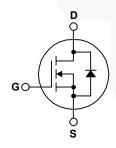
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- 24 A, 80 V,  $R_{DS(on)}$  = 60 m $\Omega$  (Max.) @V<sub>GS</sub> = 10 V,  $I_D$ = 12 A
- Low Gate Charge (Typ. 19 nC)
- · Low Crss (Typ. 50 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQP24N08	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		80	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		24	Α
	- Continuous (T <sub>C</sub> = 100°C)		17	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	96	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	single Pulsed Avalanche Energy (Note 2) 230		mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	24	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		75	W
	- Derate above 25°C		0.5	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
т.	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C
T <sub>L</sub>			300	

### **Thermal Characteristics**

Symbol	Parameter	FQP24N08	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.0	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

## **Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP24N08	FQP24N08	TO-220	Tube	N/A	N/A	50 units

### Electrical Characteristics To = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80			V
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.08		V/°C
I <sub>DSS</sub> Zero (	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1	μΑ
		V <sub>DS</sub> = 64 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nΑ
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nΑ
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A		0.048	0.06	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 12 A		12		S
C <sub>iss</sub>	Input Capacitance Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		580 210	750 270	pF pF
		$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$				•
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1.0 WITE		50	65	pF
Switchi	ing Characteristics Turn-On Delay Time			10	30	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 40 \text{ V}, I_D = 24 \text{ A},$		105	220	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 25 \Omega$		30	70	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		35	80	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 64 V, I <sub>D</sub> = 24 A,		19	25	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		4.2		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		9.6		nC
Drain-S	ource Diode Characteristics and Ma	ximum Ratings				
l <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				24	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward	Current			96	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 24 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 24 A,		63		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		130		nC

- Notes: Notes: Notes: A Repetitive Rating: Pulse width limited by maximum junction temperature. 
  2. L = 0.55 mH,  $I_{AS}$  = 24 A,  $V_{DD}$  = 25 V,  $R_G$  = 25  $\Omega$ , starting  $T_J$  = 25°C. 
  3.  $I_{SD}$  ≤ 24 A, di/dt ≤ 300 A/ $\mu$ s,  $V_{DD}$  ≤ BV $_{DSS}$ , starting  $T_J$  = 25°C. 
  4. Essentially independent of operating temperature.

## **Typical Characteristics**

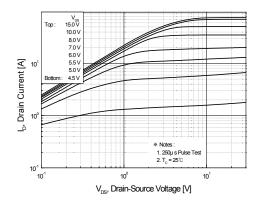


Figure 1. On-Region Characteristics

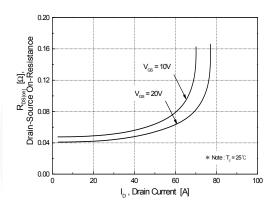


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

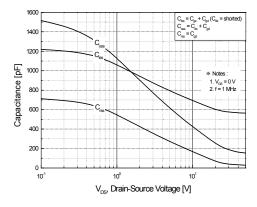


Figure 5. Capacitance Characteristics

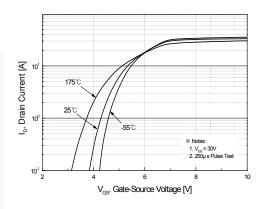


Figure 2. Transfer Characteristics

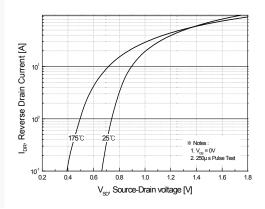


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

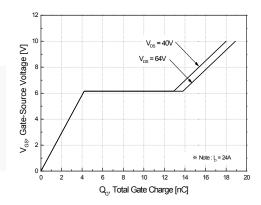


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)

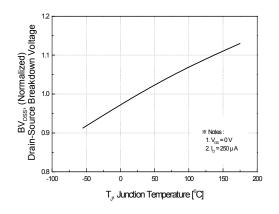


Figure 7. Breakdown Voltage Variation vs. Temperature

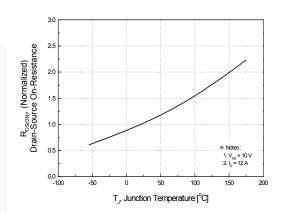


Figure 8. On-Resistance Variation vs. Temperature

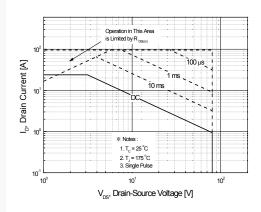


Figure 9. Maximum Safe Operating Area

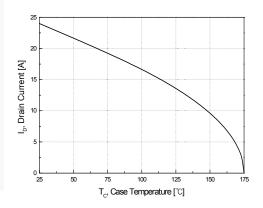


Figure 10. Maximum Drain Current vs. Case Temperature

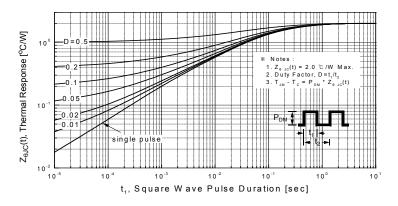


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

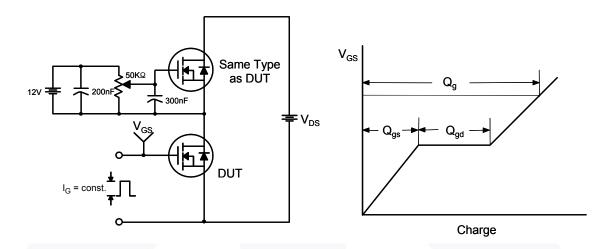


Figure 13. Resistive Switching Test Circuit & Waveforms

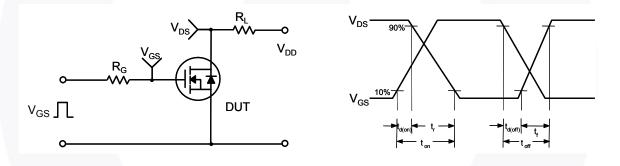
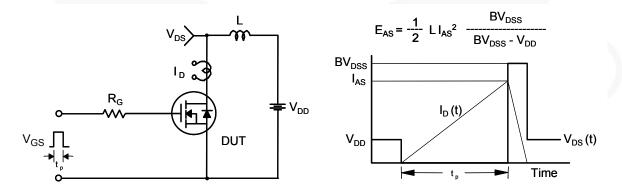


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



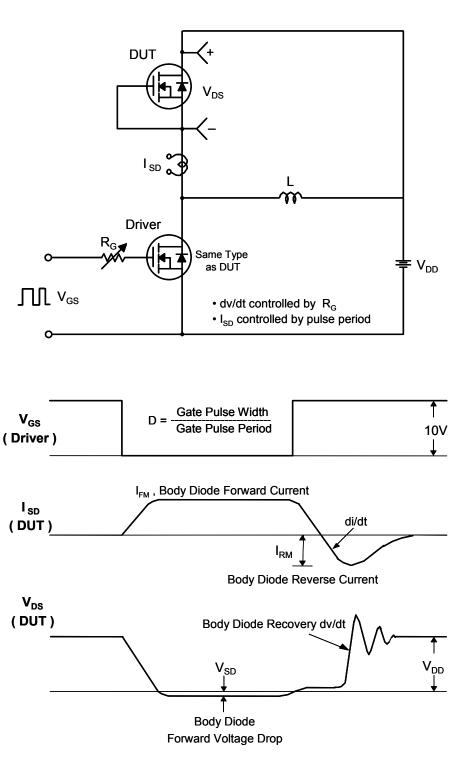


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**

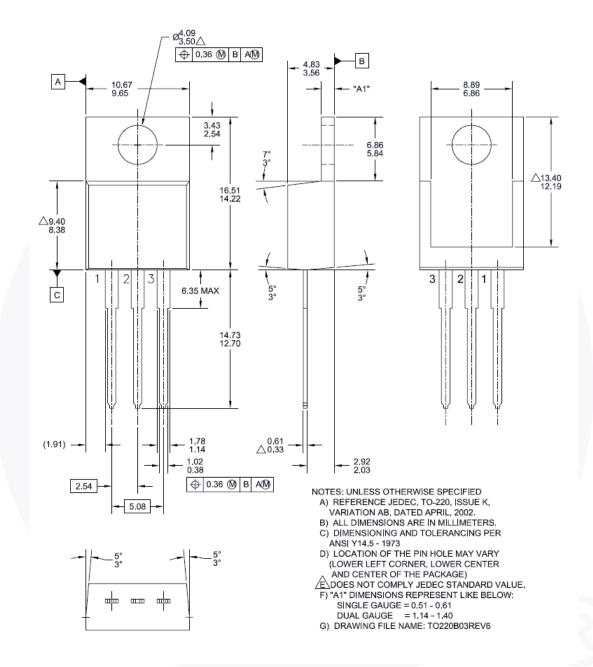


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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Dimension in Millimeters





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